IN THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application

Listing of Claims:

- 1. (Currently Amended) A semiconductor light-emitting device comprising:
- a substrate made of group III-V nitride semiconductor;
- a first n-type semiconductor layer containing indium and formed over a main surface of the substrate; and
- a light-emitting layer formed between over the first n-type semiconductor layer and the substrate.
 - 2. (Original) The device of claim 1, wherein the substrate is made of gallium nitride.
 - 3. (Original) The device of claim 1, wherein the main surface of the substrate is polished.
 - 4. (Original) The device of claim 3, wherein the main surface of the substrate is etched.
 - 5. (Original) The device of claim 3, wherein the main surface of the substrate is planarized.
 - 6. (Original) The device of claim 1,

wherein the light-emitting layer has a multiple quantum well structure formed by alternately stacking a quantum well layer and a barrier layer, and

the quantum well layer has a thickness of 1 to 2.5 nm inclusive.

7. (Currently Amended) The device of claim 1, wherein the first n-type semiconductor layer is made of a compound whose general

formula is represented by $In_aAl_bGa_{1-a-b}N$ (0<a<1, 0≤b<1, a+b≤1) (0<a<1, 0≤b<1, a+b≤1).

- 8. (Original) The device of claim 7, wherein the aluminum content of the first n-type semiconductor layer is 3% or lower.
- 9. (Original) The device of claim 1, wherein the first n-type semiconductor layer has a thickness of 10 nm to 1 μm inclusive.
- 10. (Original) The device of claim 1, further comprising a second n-type semiconductor layer formed between the substrate and the first n-type semiconductor layer.
- 11. (Original) The device of claim 10, wherein the second n-type semiconductor layer is made of a compound whose general formula is represented by In_cAl_dGa_{1-c-d}N (0≤c<1, 0≤d<1, c+d<1).</p>
 - 12. (Original) The device of claim 11, wherein the second n-type semiconductor layer is an n-type contact layer.
- 13. (Original) The device of claim 8, further comprising a third n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer.
 - 14. (Original) The device of claim 13, wherein the third n-type semiconductor layer is an n-type contact layer.
- 15. (Original) The device of claim 1, further comprising a fourth n-type semiconductor layer formed between the first n-type semiconductor layer and the light-emitting layer.
 - 16. (Original) The device of claim 15,

wherein the fourth n-type semiconductor layer is made of a compound whose general formula is represented by $Al_eGa_{1-e}N$ ($0 \le e < 1$).

- 17. (Original) The device of claim 16, wherein the fourth n-type semiconductor layer is a cladding layer.
- 18. (Original) The device of claim 17, wherein the cladding layer has a thickness of 5 to 200 nm inclusive.
- 19. (Original) The device of claim 1, further comprising:

an n-type contact layer which is formed between the substrate and the light-emitting layer and a portion of which is exposed;

an n-side electrode formed on the exposed portion of the n-type contact layer;

an n-type cladding layer formed between the first n-type semiconductor layer and the light-emitting layer;

- a p-type semiconductor layer formed on the light-emitting layer; and
- a p-side electrode formed over the p-type semiconductor layer,

wherein the device is mounted with an element formation surface thereof facing a submount for mounting.

20. (Currently Amended) A illuminating device comprising the multiple semiconductor light-emitting devices of claims 1-19 claim 1.